# imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

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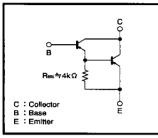
## Power Transistor (-40V, -2A)

### 2SB1183 / 2SB1239 / 2SB786F

#### Features

- 1) Darlington connection for high DC current gain.
- 2 ) Built-in 4 k $\Omega$  resistor between base and emitter.
- 3) Complements the 2SD1759/2SD1861/2SD947F.

#### Circuit schematic



Paran	neter	Symbol	Limits	Unit		
Collector-base voltage		Vсво	-40	V		
Collector-emitter	voltage	VCER	-40	V		
Emitter-base volta	age	VEBO	-5	V		
Collector current		lc	-2	A (DC)		
		Ю	-3	A (Pulse) * 1		
	2SB1183		1	W		
			10	W (Tc=25°C)		
Collector power	2SB1239	Pc	1	W *2		
dissipation	2SB786F		1.2	W		
	236/60		5	W(Tc=25°C)		
Junction temperature Storage temperature		Тј	150	τ		
		Tstg	-55~150	۲ ا		

ΑΤ٧

T146

1k-

TO-126FP

1k~

Packaging specifications and hre collector plating 1cm<sup>2</sup> or larger. Туре 2SB1183 2SB1239 2SB786F CPT3

1k~200k

π

Package

hre

Code

#### ●Electrical characteristics (Ta=25℃)

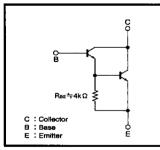
					Basic ordening drint (pieces) 2500	2500	1 1000		
Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions	-	
Collector-base	breakdown voltage	ВУсво	-40	—	—	V	Ic=-50 μ A	-	
Collector-emitte	er breakdown voltage	BVCER	-40	_		V	lc=-1mA, RBE=10kΩ	_	
Emitter-base b	reakdown voltage	BVEBO	-5		—	v	lε=−50 μ A	-	
Collector cutoff	f current	Ісво	- 1	—	-1	μA	Vc8=-24V	-	
Emitter cutoff c	urrent	(EBO		<u> </u>	1	μA	V <sub>EB</sub> =-4V	-	
Collector-emitte	er saturation voltage	VCE(eal)	-	_	-1.5	v	Ic/Is=-0.6A/-1.2mA	-	
DC current	2SB1183	<b>B</b> asis	1000	1 —	20000	_	N-4	-	
transfer ratio	2SB1239,2SB786F	hr∈.	1000	_	—		$V_{CE}/I_C = -2V/-0.5A$		
Output capacita	ance	Cob	<u> </u>	11		pF	$V_{CB} = -10V$ , $I_E = 0A$ , $f = 1MHz$	-	

## Power Transistor (40V, 2A) 2SD1759 / 2SD1861 / 2SD947F

#### Features

- 1) Darlington connection for high DC current gain.
- 2) Built-in 4kΩ resistor between base and emitter.
- 3 Complements the 2SB1183/2SB1239/2SB786F.

#### Circuit schematic



#### ●Absolute maximum ratings (Ta=25℃)

Parameter		Symbol	Limits	Unit	
Collector-base voltage		Vceo	40	V	
Collector-emitter voltage		VCER	40	$V(R_{BE}=10k\Omega)$	
Emitter-base volta	age	VEBO	5	v	
Collector current			2	A (DC)	
		lc	3	A (Puise) *1	
Collector power dissipation	2SD1861		1	*2	
	2SD1759	Pc	1	- w -	
			10	W(Tc=25°C)	
	0000475		1.2	w	
	2SD947F	1	5	W(Tc=25°C)	
Junction temperature		Tj	150	ΰ	
Storage temperat	ure	Tstg		τ	
*1 Sigle pulse Pw Packaging sp			Printed circuit boa collector plating 1		

Туре	2SD1759	2SD1861	2SD947F
Package	СРТЭ	ATV	TO-126FP
hre	1k~200k	1 k~-	1k~-
Code	ΤL	TV2	
Basic ordering unit (pieces)	2500	2500	1000

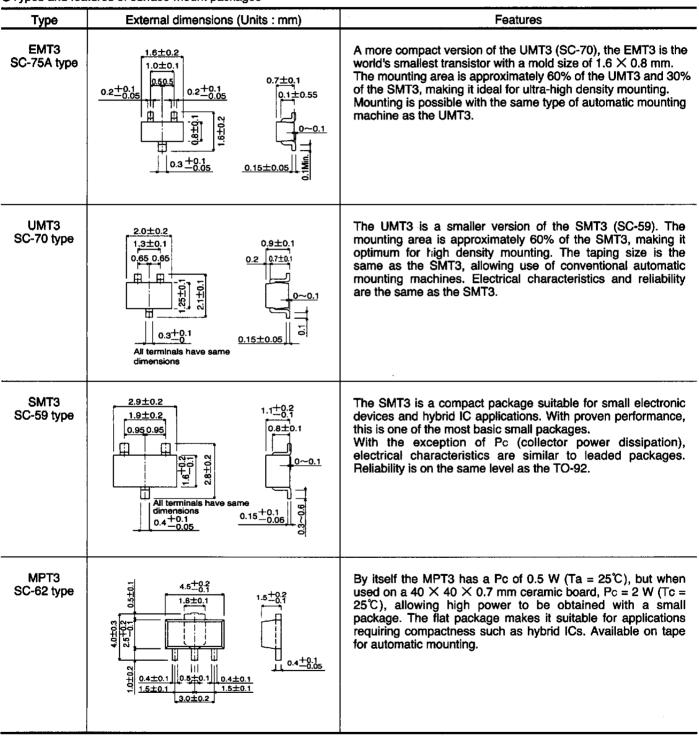
#### ●Electrical characteristics (Ta=25℃)

Pa	rameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base	breakdown voltage	ВУсво	40	—		v	Ic=50 μA	
Collector-emitte	er breakdown voltage	BVCEO	40	—	- 1	v	Ic=1mA, Rec=10kΩ	
Emitter-base b	reakdown voltage	BVEBO	5	—	-	ν	IE=50 μ A	
Collector cutoff current		Ісво		—	1	μA	VcB=24V	
Emitter cutoff c	urrent	IEBO	-	_	1	μA	VEB=4V	
Collector-emitte	er saturation voltage	VCE(set)		—	1.5	V	Ic/Is=0.6mA/1.2mA	
DC current	2SD1759		1000	—	20000			
transfer ratio	2SD1861,2SD947F	hfe	1000			_	VcE/Ic=3V/0.5A	
Output capacita	Output capacitance		-	11		pF	Vcs=10V, i=0A, i=1MHz	

(96-126-B23)

## Packages

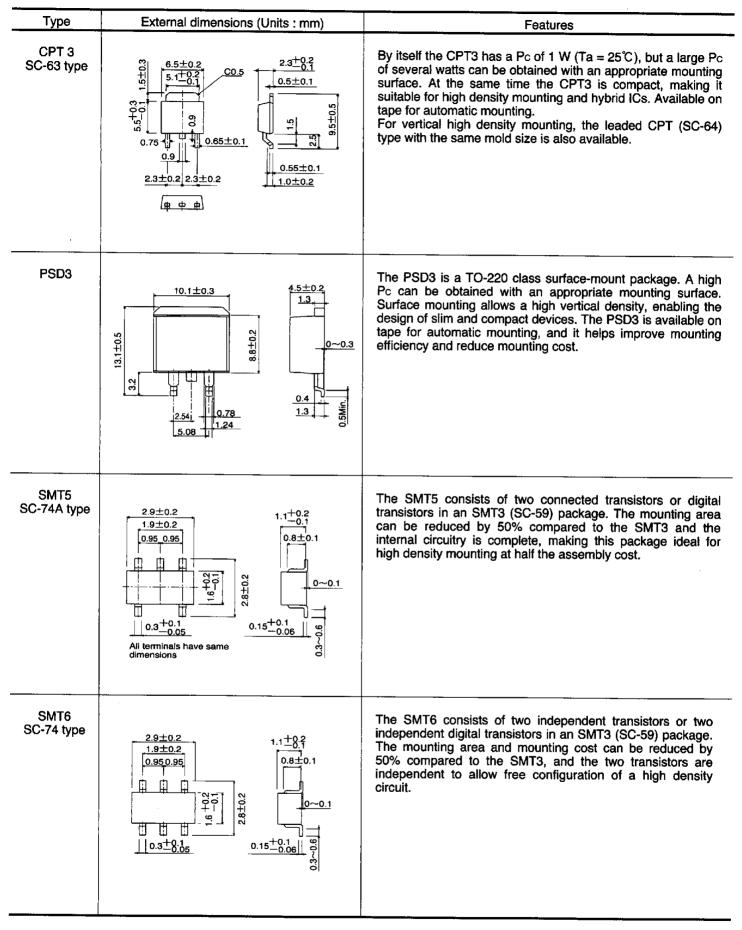
ROHM has been manufacturing transistors since 1975. In the development of products, we constantly strive to anticipate the needs of our customers. Regarding packages, the demands of the market for compactness, low power consumption, low power dissipation and automatic mounting support are becoming ever greater, and we are strengthening our product development system to meet these needs.



Types and features of surface-mount packages

**EXPLANATION** 

### Transistors

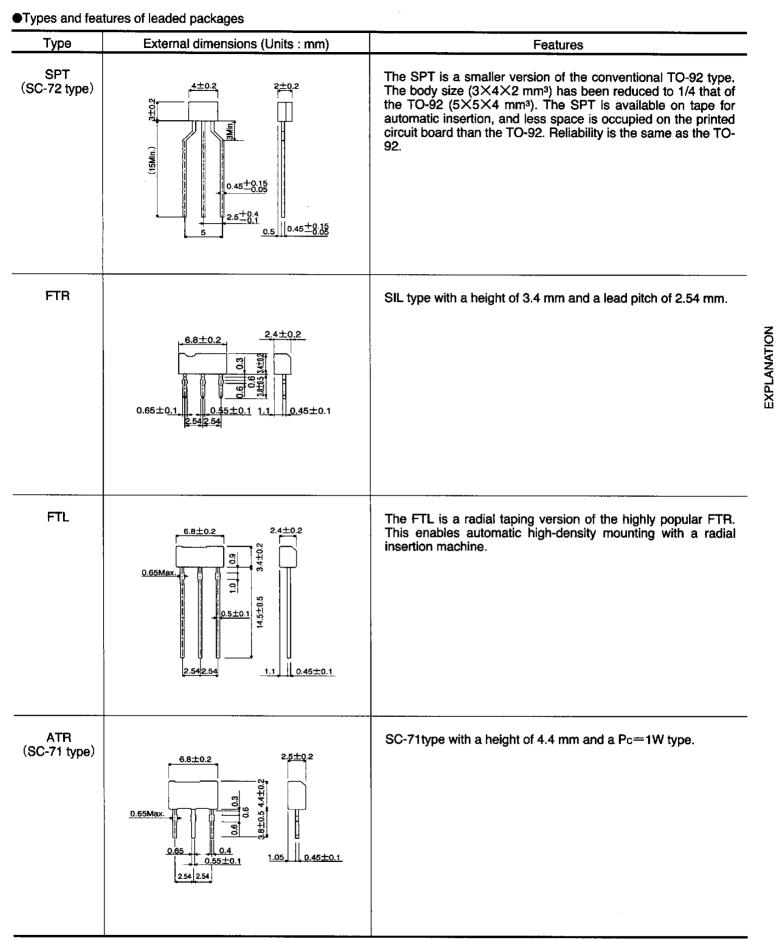


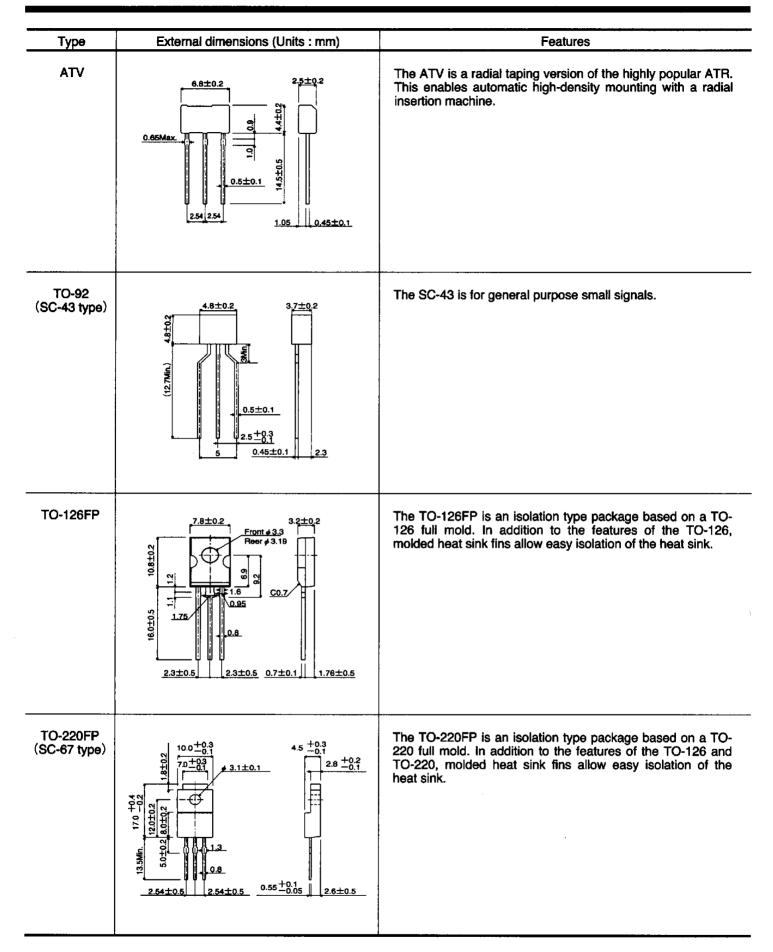
## Transistors

Туре	External dimensions (Units : mm)	Features
UMT5 SC-88A type	2.0 $\pm$ 0.2 1.3 $\pm$ 0.1 0.65 0.65 0.65 0.65 0.7 0.7 0.7 0.7 0.7 0.7 0.7 0.7	The UMT5 consists of two connected transistors or digital transistors in a UMT3 (SC-70) package. The mounting area can be reduced by 50% compared to the UMT3 and the internal circuitry is completed, making this package ideal for high density mounting at half the assembly cost.
UMT6 SC-88 type	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	The UMT6 consists of two independent transistors or two independent digital transistors in a UMT (SC-70) package. The mounting area and mounting cost can be reduced by 50% compared to the UMT3, and the two transistors are independent to allow free configuration of a high density circuit.

### Transistors

Packages





## Transistors

Туре	External dimensions (Units : mm)	Features
TO-220FN	$\begin{array}{c} 10.0 \stackrel{+0.3}{-0.1} \\ 4.5 \stackrel{+0.3}{-0.1} \\ 2.8 \stackrel{+0.2}{-0.1} \\ \hline \\ \hline \\ \\ 2.54 \stackrel{+0.2}{-0.1} \\ \hline \\ \\ \\ 2.54 \stackrel{+0.3}{-0.1} \\ \hline \\ \\ \\ 2.54 \stackrel{+0.3}{-0.1} \\ \hline \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ $	The TO-220FN features the same performance as the TO- 220FP with approximately 2 mm less height, allowing the design of slimmer devices. Furthermore, the elimination of support pins in the fin (collector electrode) solves short- circuiting problems with neighboring components and the chassis. To make the height to the installation hole the same as the TO-220FP, it can be replaced as is from the TO-220FP.